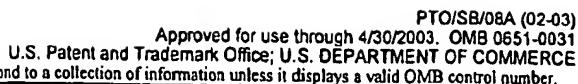


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Sheet

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## Application Number

10/628.020

Filing Date

July 25, 2003

First Named Inventor

Yeo, et al.

### Art Unit

2811

Examiner Name \_\_\_\_\_

TBD

Attorney Docket Number

**TSM03-0555**

Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	'Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code <sup>2</sup> (if known)			
CJH	1	US-4,314,269	02-02-1982	Fujiki	
	2	US-4,631,803	12-30-1986	Hunter, et al.	
	3	US-4,946,799	08-07-1990	Blake, et al.	
	4	US-5,447,884	09-05-1995	Fahey, et al.	
	5	US-5,461,250	10-24-1995	Burghartz, et al.	
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	14	US-6,059,895	05-09-2000	Chu, et al.	
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	16	US-6,232,163 B1	05-15-2001	Voldman, et al.	
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21		US-6,413,802 B1	07-02-2002	Hu, et al.	
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**Examiner  
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Date  
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# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet

2

of

**5**

**Complete if Known**

Application Number

10/628,020

Filing Date

**July 25, 2003**

**First Named Inventor**

Yeo, et al.

### Art Unit

2811

**Examiner Name**

TBD

Attorney Docket Number

**TSM03-0555**

## U.S. PATENT DOCUMENTS

[illegible]

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Signature**

Andy Munn

Date Considered

12/02/02

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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>		Application Number	10/628,020
		Filing Date	July 25, 2003
		First Named Inventor	Yeo, <i>et al.</i>
		Group Art Unit	2811
		Examiner Name	TBD
		Attorney Docket Number	TSM03-0555
Sheet	3	of	5

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cita. No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	2
ah	32	ISMAIL, K., <i>et al.</i> , "Electron Transport Properties of Si/SiGe Heterostructures: Measurements and Device Implications," Applied Physics Letters, Vol. 63, No. 5, (August 2, 1993), pp. 660-662.	
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Examiner Signature	Andy Kung		Date Considered 12/01/03

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Substitute for form 1449B/PTO				<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>				Application Number	10/628,020
				Filing Date	July 25, 2003
				First Named Inventor	Yeo, <i>et al.</i>
				Group Art Unit	2811
				Examiner Name	TBD
Sheet	4	of	5	Attorney Docket Number	TSM03-0555

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>	
ah	45	MATTHEWS, J.W., <i>et al.</i> , "Defects in Epitaxial Multilayers – III. Preparation of Almost Perfect Multilayers," Journal of Crystal Growth, Vol. 32, (1976), pp. 265-273.		
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ah	57	"Future Gate Stack," International Sematech, 2001 Annual Report.		
Examiner Signature			Date Considered	12/02/02

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Substitute for form 1449B/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>				<b>Complete if Known</b>	
				Application Number	10/628,020
				Filing Date	July 25, 2003
				First Named Inventor	Yeo, <i>et al.</i>
				Group Art Unit	2811
				Examiner Name	TBD
				Attorney Docket Number	TSM03-0555
Sheet	5	of	5		

[illegible]

Examiner Signature	<i>Anders Nyman</i>	Date Considered	<i>12/02/02</i>
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## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Application Number	10/628,020
Filing Date	July 25, 2003
First Named Inventor	Yeo, <i>et al.</i>
Art Unit	2811
Examiner Name	Unknown
Attorney Docket Number	TSM03-0555

Sheet	1	of	1	Attorney Docket Number	TSM03-0555
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## U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code <sup>2</sup> (if known)			
AL	A	US-6,258,664 B1	07-10-2001	Reinberg	
	B	US-6,358,791 B1	03-19-2002	Hsu, <i>et al.</i>	
	C	US-2002/0153549 A1	10-24-2002	Laibowitz, <i>et al.</i>	
	D	US-6,475,838 B1	11-05-2002	Bryant, <i>et al.</i>	
	E	US-2003/0030091 A1	02-13-2003	Bulsara, <i>et al.</i>	
	F	US-6,524,905 B2	02-25-2003	Yamamichi, <i>et al.</i>	
	G	US-6,558,998 B2	05-06-2003	Belleville, <i>et al.</i>	
		US-			
		US-			
		US-			
		US-			

## FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup> - Number <sup>4</sup> - Kind Code <sup>5</sup> (if known)				
AL	H	WO 03/017336 A2	02-27-2003	Amberwave Systems Corporation		

## OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite, No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
	I	WANG, L.K., <i>et al.</i> , "On-Chip Decoupling Capacitor Design to Reduce Switching-Noise-Induced Instability in CMOS/SOI VLSI," Proceedings of the 1995 IEEE International SOI Conference, Oct. 1995, pp. 100-101.	
	J	YEOH, J.C., <i>et al.</i> , "MOS Gated Si:SiGe Quantum Wells Formed by Anodic Oxidation," Semicond. Sci. Technol. (1998), Vol. 13, pp. 1442-1445, IOP Publishing Ltd., UK.	
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Examiner Signature		Date Considered	12/02/02
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